

# Sreyas Institute of Engineering and Technology An Autonomous Institution

Approved by AICTE, Affiliated to JNTUH Accredited by NAAC-A Grade, NBA (CSE, ECE & ME) & ISO 9001:2015 Certified

#### DEPARTMENT OF ELECTRONICS AND COMMUNICATION ENGINEERING

## EXPERTS FEEDBACK ON INNOVATIVE METHODS IN TEACHING AND LEARNING PROCESS

Please fill out this feedback form so we ensure quality methodologies in teaching and learning process

Email ID: maruthirao. chinnam D Sreyas, ac. in NAME OF THE EXPERT: CH. S.V. Maruthi Rao. Innovative Method: Surprise test

Parameters/Ratings	Excellent	Good	Fair	Poor
How would you rate this innovative method?	/	1		
How satisfied were you with the clear goals?		/		. 1
How satisfied were you with appropriate usage?			70-1	13.51
How satisfied were you with implementation?			Tell	-17787
How satisfied were you with outcomes?	12.4	70 / 6	STALK.	- September
How satisfied were you with the timeliness?	/	1		THE P
Would you recommend our innovative method to others?	YES/NO			
Please provide any additional comments or suggestions.	Good 'n	novative	teachin Method	٠,

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### INNOVATIONS BY THE FACULTY IN TEACHING & LEARNING EXPERT REVIEW ANALYSIS & ACTION TAKEN REPORT

Academic Year: 2024-25 Year: III

Semester: J

Section: B

Faculty Name: Ch. S. V. Maruthi Rasubject & Topic: Cmas VLS1

Methodology: Surprise test

**Analysis Report Over Experts** 

#### **Expert Review 1: Observations:**

1.

2. Helps to understand the topic easily.

3.

#### **Expert Review 2: Observations:**

1.

2. Increased in the creativity.

3.

#### **Expert Review 3: Observations:**

1.

2. Helped in Analysis of the Subject

3.

Result of Satisfactory: Excellent / Very Good/ Good/ Satisfactory/ Not Satisfactory

#### **Action Taken Report:**

It can implemented for more and more subjects

Head of the Depterment
Electronics & Communi HO Fing Treing
Sreyas Institute of Engineering and Technology
Beside Indu Aranya, Nagole, Hyderabad-500068.

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### INNOVATIONS BY THE FACULTY IN TEACHING & LEARNING STUDENTS FEED BACK ANALYSIS REPORT & ACTION TAKEN REPORT

Academic Year: 2024 -26 Year: III

Semester: II

Section: B

Faculty Name: Ch. S. V. Maruth: Rao Subject & Topic: CMOS VLSI

Methodology:

Total number of students : 55

Number of students present: 55

Number of students absent: 10

Maximum Score

<u>,</u>

**Obtained Score** 

: 791/.

% of Satisfactory

: Very Good

Result of Satisfactory: Excellent/ Very Good/ Good/ Satisfactory/Not Satisfactory

Levels of Satisfactory: <50% = Not Satisfactory; >50 to <60% = Satisfactory; >60 to <70%

= Good;

>70 to <80% = Very Good; & >80 to <100= Excellent

Analysis Report:

1.

2. Helps in Analysis of Subject

3.

Action Taken Report:

Improved in the sequence of various subjects

Head of the Partment

Electronics & Communication Engineering

Sreyas Institute of Engineering and Technology

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### **Quiz questions**

For FET, input current I <sub>G</sub> =	
a. High	
b. Low	
c. Zero	
d. Infinite	
In region, FET acts as voltage v	ariable resistor
a. Linear	
b. Ohmic	
c. Saturation	
d. Cutoff	
Depletion MOSFET works in	
a. Depletion mode only	
b. Enhancement mode only	
c. Both modes	
d. None	
The input impedance of E MOSFET is	D MOSFET
a. Less than	
b. Greater than	
c. Equal to	
d. Less than or equal to	
FET is temperature stable as con	npared to BJT.
a. More	
b. Less	
c. Equal	
d. None	
Channel is permanently present in	MOSFET
a. E MOSFET	
b. D MOSFET	
c. Both	
d. None	
Enhancement MOSFET works in	
a. Depletion mode only	
b. Enhancement mode only	
c. Both modes	
d. None	

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In region JFET acts as an amplifier	
a. Cutoff	
b. Linear	
c. Ohmic	
d. Saturation	
The current in JFET is due to	
a. Majority charge carriers	
b. Minority charge carriers	
c. Both	
d. None	
E MOSFET starts conducting current when	
a. VGS≤Vth	
b. VGS≥ Vth	
c. Vth≤0	
d. Any of the above	
If Vo=0, the transistor is said to be in state	
a. On b. Off	
c. High Impedance	
d. None	
Phase shift of 180° between input and output occurs in which configuration?	
a. CB	
b. CE	
c. CC	
d. CD	
In active region transistor acts as	
a. Amplifier	
b. Switch	
c. Rectifier	
d. None In punch through effect, if voltage is increased rapidly, thenterminal disappearance.	ars
a. Emitter	
b. Base	
c. Collector	
d. Source	
The current gain in CB configuration is	
a. Unity	
b. less than unity	



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c. greater than unity d. none	
Early effect occurs in configuration.	
is transferred in transistors.	
BJT is a device.	
Output parameters of common emitter are	
Current gains of CB, CE, CC are	<u> </u>
The advantage of E-MOSFET is	
JFET works withbias.	
When MOSFET is used as a capacitor, the 3 operating m	
The advantage of JFET over BJT is	
Input resistance of MOSFET is very high because	
The insulated material in MOSFET is made up of	material.
When VGS in JFET is made sufficiently negative ID is r	reduced to
FET is controlled device.	
Abbreviation of JFET	
Abbreviation of E-MOSFET	



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